List of chemicals to be used in CEN for Lithography process:

- **Resist: AR-N 7520.11 new, quantity 250 ml**

  Negative E-Beam Resist, mix & match,
  high resolution, etch resistant
  Composition: **2-Methoxy-1-Methylethyl acetate**

- **Developer: AR 300-47, quantity 1 liter**

  Developer for photo- and e-beam resist
  Composition : Tetramethylammonium hydroxide

- **Remover: AR 300-76, quantity 1 liter**

  Remover for photo- and e-beam resist
  Composition : **Dibasic Esters (DBE)**

Remark: Above all mentioned chemicals are carbon or hydrogen-based polymer and it doesn't contain any metal element such as Na, K, Cu etc. These are CMOS compatible materials, also obey the IITBNF contamination policy and non-harmful.